

WHAT IS CLAIMED IS:

1           1. A semiconductor integrated circuit device comprising:  
2           a trench formed in a semiconductor substrate and defining active regions and  
3 dummy regions;  
4           an element isolation insulating film buried in said trench such that said  
5 element isolation insulating film serves as an element isolation region;  
6           an interlayer insulating film covering said substrate and said dummy regions  
7 and including an insulating film planarized; and  
8           external terminals formed over said interlayer insulating film such that said  
9 dummy regions are formed under said external terminals.

1           2. A semiconductor integrated circuit device according to claim 1, wherein a  
2 length of said dummy region is shorter than a distance between said external  
3 terminals.

1           3. A semiconductor integrated circuit device comprising:  
2           a trench formed in a semiconductor substrate and defining active regions and  
3 dummy regions;  
4           an element isolation insulating film buried in said trench such that said  
5 element isolation insulating film serves as an element isolation region;  
6           an interlayer insulating film covering said substrate and said dummy regions;  
7 and  
8           an external terminal formed over said interlayer insulating film such that said  
9 dummy regions are formed under said external dummy regions and such that  
10 dummy interconnections each comprised of a same layer as external terminal are  
11 not formed at said scribing area.

1           4. A semiconductor integrated circuit device comprising:  
2           a trench formed in a semiconductor substrate and defining active regions and

3 dummy regions;  
4 an element isolation insulating film buried in said trench such that said  
5 element isolation insulating film serves as an element isolation region;  
6 an interlayer insulating film covering said substrate and said dummy regions;  
7 external terminals formed over said interlayer insulating film such that said  
8 dummy regions are formed under said external terminals;  
9 interconnections each comprised of a same layer as external terminal and  
10 formed over said interlayer insulating film; and  
11 dummy interconnections each comprised of a same layer as external terminal  
12 and spaced from said interconnections.

1 5. A semiconductor integrated circuit device according to claim 4, wherein a  
2 length of said interconnection is shorter than a distance between said external  
3 terminals.

1 6. A semiconductor integrated circuit device comprising:  
2 a trench formed in a semiconductor substrate and defining active regions and  
3 dummy regions;  
4 an element isolation insulating film buried in said trench such that said  
5 element isolation insulating film serves as an element isolation region;  
6 gate electrodes formed over said active regions and serving as gate  
7 electrodes of MISFET type elements; and  
8 dummy patterns each comprised of a same layer as said gate electrodes and  
9 formed in a region spaced from said gate electrodes and a marker portion for  
10 photolithography.